# ODB5763UX3.A3

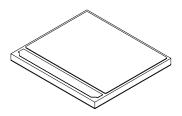
**OS-CORE® UX:3** 

#### Features:

- Polarity: p-side up
- Chip technology: UX:3
- Color: blue
- Chipsize: 57 mil x 63 mil

## **Ordering Information**

Type ODB5763UX3.A3-MM-MM-1-C Ordering Code Q65112A3663





## **Maximum Ratings**

Parameter	Symbol		Values
Operating Temperature	T <sub>op</sub>	min.	-40 °C
		max.	125 °C
Storage Temperature <sup>1)</sup>	T <sub>stg</sub>	min.	-40 °C
		max.	125 °C
Recommended Die Storage Temperature ≤ 60% RH	$T_{stgdie}$	max.	30 °C
Junction Temperature	T <sub>j</sub>	max.	150 °C
Junction temperature for short time applications*	T <sub>j</sub>	max.	175 °C
Forward Current	I <sub>F</sub>	min.	50 mA
T <sub>J</sub> = 25 °C	·	max.	6000 mA
Forward Current Pulsed t $\leq$ 10 µs; D = 0.005 ; T <sub>j</sub> = 25 °C	I <sub>F pulse</sub>	max.	8000 mA
ESD withstand voltage acc. ANSI/ESDA/JEDEC JS-001 (HBM, Class 0)	$V_{ESD}$		ESD sensitive device
Reverse voltage 2)	V <sub>R</sub>		Not designed for reverse operation

\*The median lifetime (L70/B50) for Tj =175°C is 100h.

#### **Characteristics**

I<sub>F</sub> = 1000 mA; T<sub>J</sub> = 25 °C

Parameter	Symbol		Values
Dominant Wavelength <sup>3)</sup> I <sub>F</sub> = 1000 mA	$\lambda_{dom}$	min. max.	440.0 nm 470.0 nm
Forward Voltage <sup>4)</sup> I <sub>F</sub> = 1000 mA	V <sub>F</sub>	min. typ. max.	2.80 V 2.95 V 3.30 V

#### **Additional Information**

Die bonding	Metalization frontside	Metalization backside
Eutectic bonding	Gold	AuSn



## Binning Table 5)3)

I<sub>F</sub> = 1000 mA

Radiant Intensity I <sub>e</sub> a. u.	Dominant Wavele λ <sub>dom</sub> nm 440.0 - 442.5	ength 442.5 - 445.0	445.0 - 447.5	447.5 - 450.0	450.0 - 452.5
60 - 67	A13	B13	C13	D13	E13
67 - 72	A16	B16	C16	D16	E16
72 - 77	A19	B19	C19	D19	E19
77 - 82	A22	B22	C22	D22	E22
82 - 87	A25	B25	C25	D25	E25
87 - 92	A28	B28	C28	D28	E28
92 - 97	A31	B31	C31	D31	E31

Radiant Intensity	Dominant Wavelengtl $\lambda_{dom}$	n		
a. u.	nm 452.5 - 455.0	455.0 - 460.0	460.0 - 465.0	465.0 - 470.0
60 - 67	F13	G13	H13	113
67 - 72	F16	G16	H16	116
72 - 77	F19	G19	H19	119
77 - 82	F22	G22	H22	122
82 - 87	F25	G25	H25	125
87 - 92	F28	G28	H28	128
92 - 97	F31	G31	H31	131

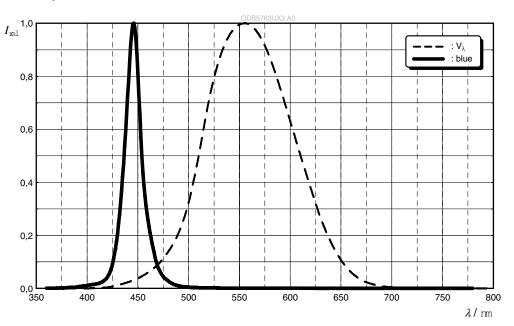
## Correlation factor <sup>6)</sup>

Unit	Value	Condition
CF (mW/sr / a.u.)	6.17	chip to air
CF (mW / a.u.)	20.57	chip with silicone lens



#### **Relative Spectral Emission**<sup>7)</sup>

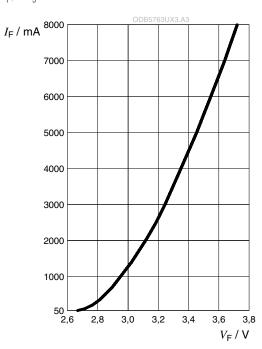
 $I_{_{rel}}$  = f ( $\lambda$ );  $I_{_F}$  = 1000 mA;  $T_{_J}$  = 25 °C





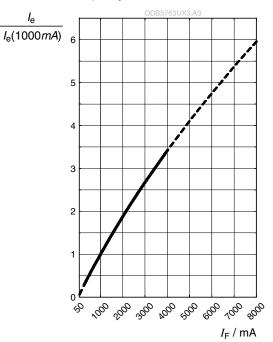
#### Forward current <sup>7), 8)</sup>

 $I_F = f(V_F); T_J = 25 \ ^{\circ}C$ 



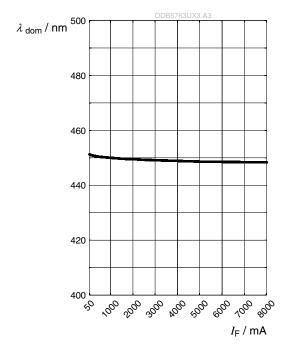
#### **Relative Radiant Intensity** <sup>7), 8)</sup>

 $I_{E}/I_{E}(1000 \text{ mA}) = f(I_{F}); T_{J} = 25 \text{ °C}$ 



#### Dominant Wavelength 7)

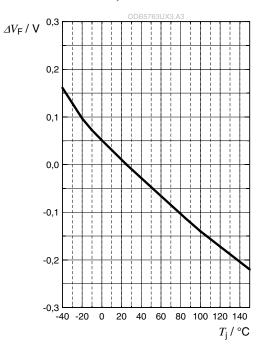
 $\lambda_{dom} = f(I_F); T_J = 25 \ ^{\circ}C$ 





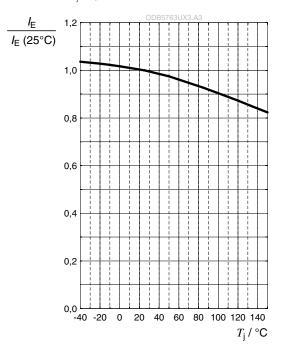
#### Forward Voltage 7)

 $\Delta V_{_{\rm F}} = V_{_{\rm F}} - V_{_{\rm F}}(25 \ ^{\circ}{\rm C}) = f(T_{_{\rm J}}); I_{_{\rm F}} = 1000 \ {\rm mA}$ 

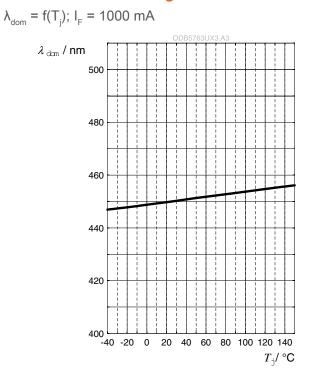


#### **Relative Radiant Intensity** <sup>7)</sup>

 $I_{E}/I_{E}(25 \text{ °C}) = f(T_{i}); I_{F} = 1000 \text{ mA}$ 

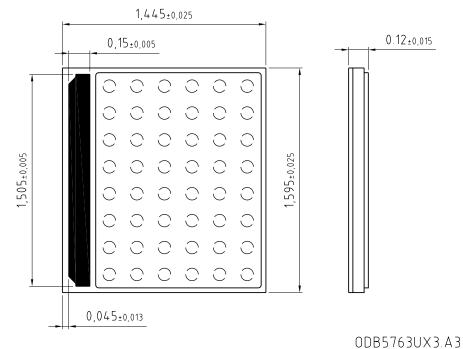


#### Dominant Wavelength 7)





## Dimensional Drawing <sup>9)</sup>



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#### Disclaimer

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Language english will prevail in case of any discrepancies or deviations between the two language wordings.

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#### Glossary

- <sup>1)</sup> **Shelf life:** Temperature refer solely to storage of finished LED product (Not valid for chip on die sheet).
- <sup>2)</sup> **Reverse Operation:** Not designed for reverse operation. Continuous reverse operation can cause migration and damage of the device.
- <sup>3)</sup> **Wavelength:** The wavelength is measured at a current pulse of typically 10 ms and with an internal reproducibility of  $\pm$  1 nm (with a coverage factor of k = 3).
- <sup>4)</sup> **Forward Voltage:** The forward voltage is measured during a current pulse of typically 5 ms and with an internal reproducibility of ± 0.1 V (with a coverage factor of k = 3).
- <sup>5)</sup> **Brightness:** Brightness values are measured during a current pulse of typically 10 ms and with an internal reproducibility of  $\pm 8$  % (with a coverage factor of k = 3).
- <sup>6)</sup> **Correlation Factor:** The exemplary correlation factor (CF) was estimated by sample build of the chip in a reference package and describes the exemplary correlation between the chip brightness measured in arbitrary units (a.u.) and the brightness in a reference package: CF = I/Φ(package) / I(chip). This factor is purely given as an indication of possible package brightness values. It may vary for different package es due to influences of geometries, reflectivity/refractive index of package materials or other material properties.
- <sup>7)</sup> Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- <sup>8)</sup> **Characteristic curve:** In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- <sup>9)</sup> **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.

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